

ABSTRACT OF THE DISCLOSURE

The present invention is; (a) a process for stabilizing a cyclotetrasiloxane,  
5 such as 1,3,5,7-tetramethylcyclotetrasiloxane, against polymerization used in a  
chemical vapor deposition process for silicon oxides in electronic material  
fabrication comprising providing an effective amount of a free radical scavenger  
polymerization inhibitor to such cyclotetrasiloxane; and (b) a composition of a  
cyclotetrasiloxane, such as 1,3,5,7-tetramethylcyclotetrasiloxane, stabilized  
10 against polymerization used in a chemical vapor deposition process as a  
precursor for silicon oxides in electronic material fabrication, comprising; such  
cyclotetrasiloxane and a free radical scavenger polymerization inhibitor.